



DMTH43M8LK3Q

Product Summary

BV _{DSS}	BV _{DSS} R _{DS(ON)} Max I	
40V	3.6mΩ @ V _{GS} = 10V	100A
	5.2mΩ @ V _{GS} = 5V	90A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Power Management Functions
- DC-DC Converters
- Backlighting

40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Ensures On State Losses are Minimized
- Excellent Q_{gd} x R_{DS(ON)} Product (FOM)
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

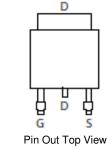
Mechanical Data

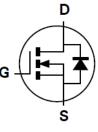
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.33 grams (Approximate)



TO252 (DPAK)

Top View





Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH43M8LK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

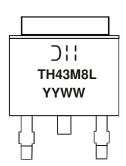
2. See http://www.clodes.com/quality/lead_free.html for more information about blodes incorporated s definitions of Halogen- and Antimony-free, Green and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



) | | = Manufacturer's Marking
TH43M8L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	40	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current, V _{GS} = 10V (Note 6)	T _A = +25°C T _A = +100°C	ID	17.6 12.5	А
Continuous Drain Current, V_{GS} = 10V (Note 7)	T _C = +25°C T _C = +100°C	I _D	100 80	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	150	A	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	70	A	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	150	A	
Avalanche Current, L=1mH	I _{AS}	13.2	A	
Avalanche Energy, L=1mH		E _{AS}	87	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	PD	3.1	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	47	°C/W
Total Power Dissipation (Note 7)	PD	88	W
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	1.7	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +175	°C

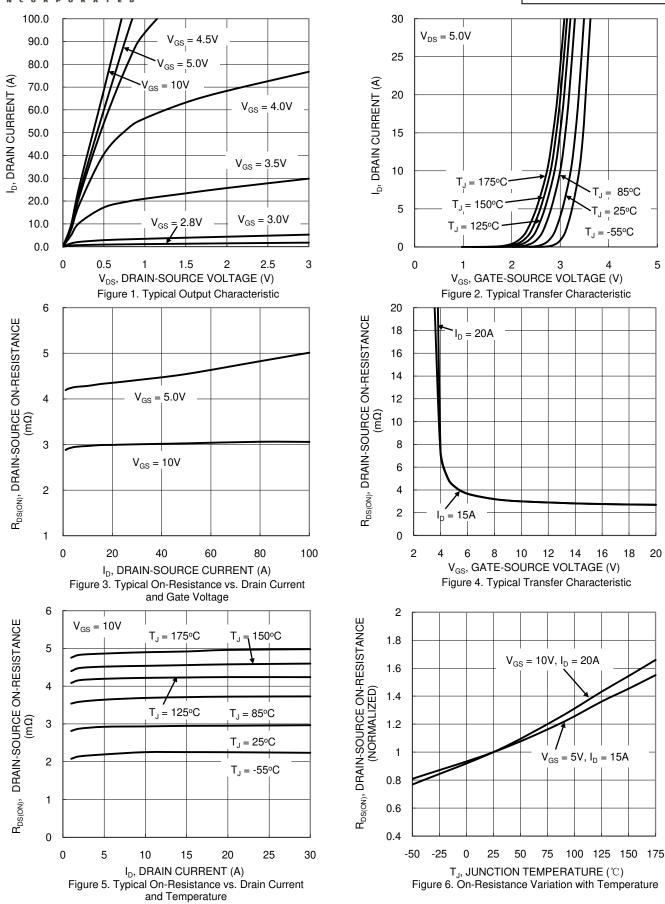
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	-	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	—	1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	—	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	—	2.9	3.6	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	4.3	5.2	mΩ	$V_{GS} = 5V, I_{D} = 15A$	
Diode Forward Voltage	V _{SD}	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	2,693	—		$\label{eq:VDS} \begin{split} V_{DS} &= 20V, \ V_{GS} = 0V, \\ f &= 1MHz \end{split}$	
Output Capacitance	Coss		1,172	—	pF		
Reverse Transfer Capacitance	C _{rss}	—	52	—			
Gate Resistance	Rg	—	2.54	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	38.5	—	nC		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	17.6	—		$V_{DS} = 20V, I_D = 20A$	
Gate-Source Charge	Qgs	_	6.9	—	nC		
Gate-Drain Charge	Q _{qd}	_	6.9	_			
Turn-On Delay Time	t _{D(ON)}	_	5.2	—		$\label{eq:VDD} \begin{split} V_{DD} &= 20V, V_{GS} = 10V, \\ I_D &= 20A, R_G = 1.6\Omega \end{split}$	
Turn-On Rise Time	t _R	_	5.7	_			
Turn-Off Delay Time	t _{D(OFF)}		23.5	_	ns		
Turn-Off Fall Time	t _F		11	_	1		
Body Diode Reverse Recovery Time	t _{RR}	_	35.4	_	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	—	32.9	—	nC	Ι _F = 15A, di/dt = 100A/μs	

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing. Notes:

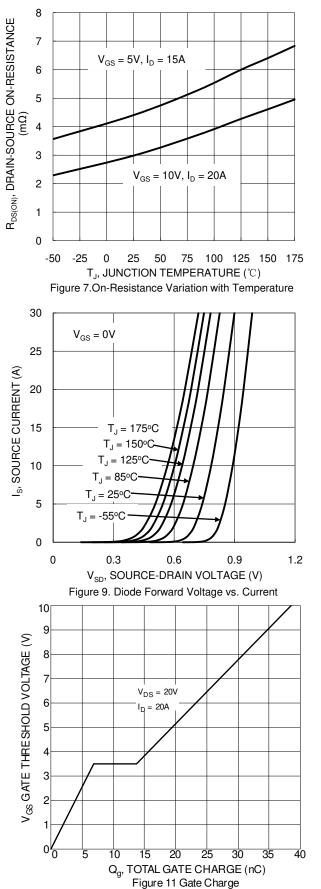


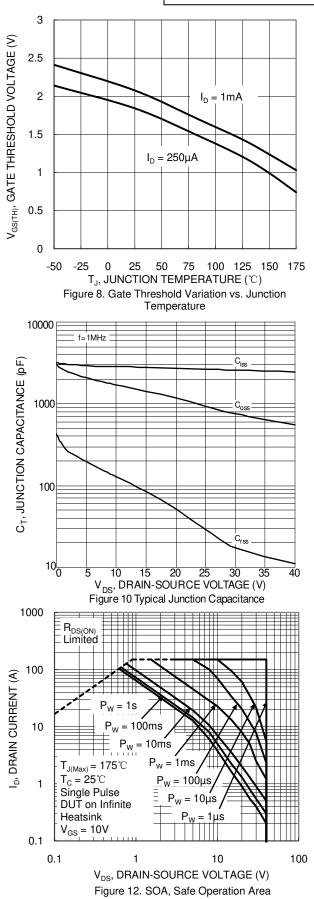




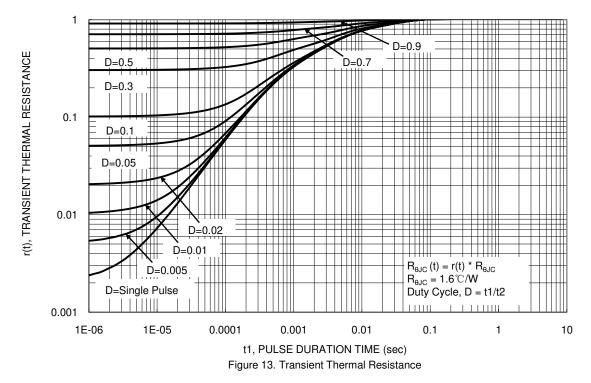


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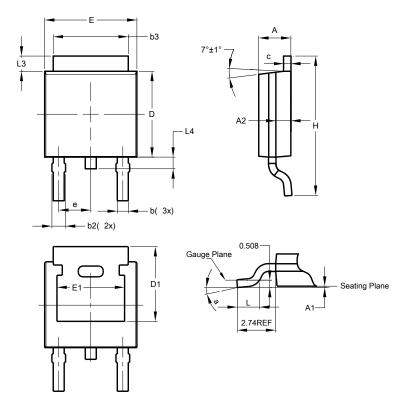




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

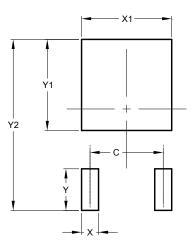


TO252 (DPAK)						
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
A1	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
b	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
С	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	-	-			
е	-	-	2.286			
Е	6.45	6.70	6.58			
E1	4.32	-	-			
Н	9.40	10.41	9.91			
L	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	-			
All	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.





Dimensions	Value (in mm)
С	4.572
Х	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700



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